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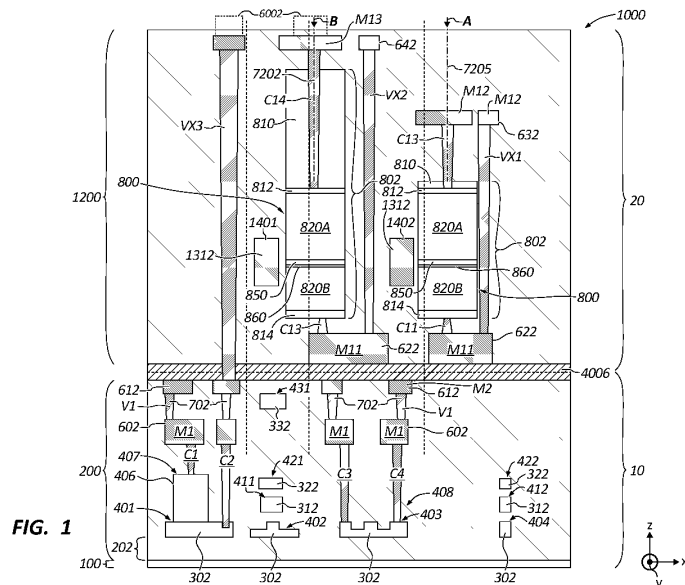
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(54) Title: PHOTONICS OPTOELECTRICAL SYSTEM



(57) Abstract: There is set forth herein a method including building a first photonics structure (10) using a first wafer having a first substrate, wherein the building the first photonics structure (10) includes integrally fabricating within a first photonics dielectric stack (200) one or more photonics device (402), the one or more photonics device (402) formed on the first substrate; building a second photonics structure (20) using a second wafer having a second substrate, wherein the building the second photonics structure includes integrally fabricating within a second photonics dielectric stack (1200) a laser stack structure active region (850) and one or more photonics device, the second photonics dielectric stack (1200) formed on the second substrate; and bonding the first photonics structure and the second photonics structure to define an optoelectrical system having the first photonics structure (10) bonded the second photonics structure (20).

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